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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

| Details | |
|----------------------------|--|
| Product Status | Active |
| Core Processor | RS08 |
| Core Size | 8-Bit |
| Speed | 20MHz |
| Connectivity | I ² C |
| Peripherals | LVD, POR, PWM, WDT |
| Number of I/O | 14 |
| Program Memory Size | 8KB (8K x 8) |
| Program Memory Type | FLASH |
| EEPROM Size | - |
| RAM Size | 254 x 8 |
| Voltage - Supply (Vcc/Vdd) | 1.8V ~ 5.5V |
| Data Converters | A/D 12x10b |
| Oscillator Type | Internal |
| Operating Temperature | -40°C ~ 85°C (TA) |
| Mounting Type | Surface Mount |
| Package / Case | 16-SOIC (0.295", 7.50mm Width) |
| Supplier Device Package | 16-SOIC |
| Purchase URL | https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mc9rs08ka8cwg |

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



1 MCU Block Diagram

The block diagram, Figure 1, shows the structure of the MC9RS08KA8 MCU.

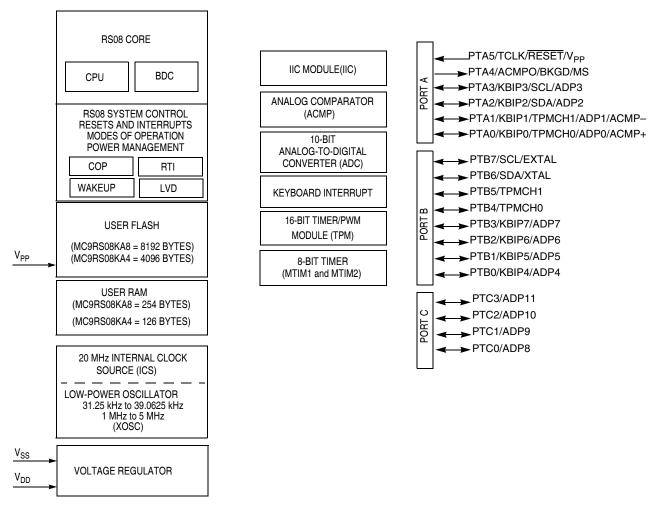


Figure 1. MC9RS08KA8 Series Block Diagram

2 Pin Assignments

This section shows the pin assignments in the packages available for the MC9RS08KA8 series.



Absolute Maximum Ratings 3.3

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 3 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this chapter.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, V_{SS} or V_{DD}) or the programmable pull-up resistor associated with the pin is enabled.

| Rating | Symbol | Value | Unit |
|--|------------------|-------------------------------|------|
| Supply voltage | V _{DD} | -0.3 to 5.8 | V |
| Maximum current into V _{DD} | I _{DD} | 120 | mA |
| Digital input voltage | V _{In} | -0.3 to V _{DD} + 0.3 | V |
| Instantaneous maximum current Single pin limit (applies to all port pins) ^{1, 2, 3} | I _D | ±25 | mA |
| Storage temperature range | T _{stg} | -55 to 150 | °C |

Table 3. Absolute Maximum Ratings

3.4 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits and it is user-determined rather than being controlled by the MCU design. In order to take P_{I/O} into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 4. Thermal Characteristics

| Rating | Symbol | Value | Unit |
|--|-------------------|---|------|
| Operating temperature range (packaged) | T _A | T _L to T _H -40 to 85 | °C |
| Maximum junction temperature | T _{JMAX} | 105 | °C |
| Thermal resistance 16-pin PDIP | $\theta_{\sf JA}$ | 80 | °C/W |
| Thermal resistance 16-pin SOIC | $\theta_{\sf JA}$ | 112 | °C/W |

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Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (VDD) and negative (VSS) clamp voltages, then use the larger of the two resistance values.

 $^{^2}$ All functional non-supply pins are internally clamped to V_{SS} and V_{DD} except the \overline{RESET}/V_{PP} pin which is internally clamped to V_{SS} only.

Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD} , the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external VDD load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low which would reduce overall power consumption.



| Rating | Symbol | Value | Unit |
|---------------------------------|-------------------|-------|------|
| Thermal resistance 16-pin TSSOP | $\theta_{\sf JA}$ | 75 | °C/W |
| Thermal resistance 20-pin PDIP | $\theta_{\sf JA}$ | 75 | °C/W |
| Thermal resistance 20-pin SOIC | $\theta_{\sf JA}$ | 96 | °C/W |

The average chip-junction temperature (TJ) in °C can be obtained from:

$$T_{J} = T_{A} + (P_{D} \times \theta_{JA})$$
 Eqn. 1

where:

 $T_A =$ Ambient temperature, °C

 θ_{JA} = Package thermal resistance, junction-to-ambient, °C /W

$$P_D = P_{int} + P_{I/O}$$

 $P_{int} = I_{DD} \times V_{DD}$, Watts chip internal power

 $P_{I/O}$ = Power dissipation on input and output pins user determined

For most applications, $P_{I/O} \ll P_{int}$ and can be neglected. An approximate relationship between PD and TJ (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_A + 273^{\circ}C)$$
 Eqn. 2

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_\Delta + 273^{\circ}C) + \theta_{J\Delta} \times (PD)^2$$
 Eqn. 3

where K is a constant pertaining to the particular part. K can be determined from Equation 3 by measuring P_D (at equilibrium) for a known T_A . Using this value of K, the values of P_D and T_J can be obtained by solving equations 1 and 2 iteratively for any value of T_A .

3.5 ESD Protection and Latch-Up Immunity

Although damage from electrostatic discharge (ESD) is much less common on these devices than on early CMOS circuits, normal handling precautions must be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits. During the device qualification ESD stresses were performed for the human body model (HBM), the machine model (MM) and the charge device model (CDM).

A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 5. ESD and Latch-up Test Conditions

| Model | Description | Symbol | Value | Unit |
|---------------|------------------------------|--------|-------|------|
| | Series resistance | R1 | 1500 | Ω |
| Human Body | Storage capacitance | С | 100 | pF |
| | Number of pulses per pin — 3 | 3 | _ | |
| | Series resistance | R1 | 0 | Ω |
| Machine | Storage capacitance | С | 200 | pF |
| | Number of pulses per pin | _ | 3 | _ |
| Lotob up | Minimum input voltage limit | _ | -2.5 | ٧ |
| Latch-up | Maximum input voltage limit | _ | 7.5 | V |

Table 6. ESD and Latch-Up Protection Characteristics

| No. | Rating ¹ | Symbol | Min | Max | Unit |
|-----|---|-----------------------|-------------------|-----|------|
| 1 | Human body model (HBM) | V_{HBM} | ±2000 | _ | V |
| 2 | Machine model (MM) | V _{MM} | ±200 | _ | V |
| 3 | Charge device model (CDM) | V _{CDM} | ±500 | _ | V |
| 4 | Latch-up current at T _A = 85°C (applies to all pins except pin 9 PTC3/ADP11) | I _{LAT} | ±100 ² | _ | mA |
| | Latch-up current at T _A = 85°C (applies to pin 9 PTC3/ADP11) | C ±100 ² — | mA | | |

Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

3.6 DC Characteristics

This section includes information about power supply requirements, I/O pin characteristics, and power supply current in various operating modes.

Table 7. DC Characteristics (Temperature Range = −40 to 85°C Ambient)

| Parameter | Symbol | Min | Typical | Max | Unit |
|--|-------------------------------|--------------|--------------|--------------|------|
| Supply voltage (run, wait and stop modes.) $0 < f_{Bus} < 10 MHz$ V_{DD} rising V_{DD} falling | V _{DD} | 2.0 1.8 | _ | 5.5 | V |
| Minimum RAM retention supply voltage applied to V _{DD} | V _{RAM} | 0.81 | _ | _ | V |
| Low-voltage Detection threshold (V _{DD} falling) (V _{DD} rising) | V _{LVD} | 1.80 1.88 | 1.86 1.94 | 1.95 2.03 | V |
| Power on RESET (POR) voltage | V _{POR} ¹ | 0.9 | _ | 1.7 | V |

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 $^{^2}$ These pins meet JESD78A Class II (section 1.2) Level A (section 1.3) requirement of ± 100 mA.

 $^{^3}$ This pin meets JESD78A Class II (section 1.2) Level B (section 1.3) characterization to ± 75 mA. This pin is only present on 20 pin package types.



Table 7. DC Characteristics (Temperature Range = −40 to 85°C Ambient) (continued)

| Parameter | Symbol | Min | Typical | Max | Unit |
|--|---|-----------------------|------------------|----------------------|------|
| Input high voltage (V _{DD} > 2.3V) (all digital inputs) | V _{IH} | $0.70 \times V_{DD}$ | _ | _ | V |
| Input high voltage (1.8 V \leq V _{DD} \leq 2.3 V) (all digital inputs) | V _{IH} | $0.85 \times V_{DD}$ | _ | _ | V |
| Input low voltage (V _{DD} > 2.3 V) (all digital inputs) | V _{IL} | _ | _ | $0.30 \times V_{DD}$ | V |
| Input low voltage (1.8 V \leq V _{DD} \leq 2.3 V) (all digital inputs) | V _{IL} | _ | _ | $0.30 \times V_{DD}$ | V |
| Input hysteresis (all digital inputs) | V _{hys} ¹ | $0.06 \times V_{DD}$ | | _ | V |
| Input leakage current (per pin) V _{In} = V _{DD} or V _{SS} , all input only pins | llinl | _ | 0.025 | 1.0 | μΑ |
| High impedance (off-state) leakage current (per pin) $V_{In} = V_{DD}$ or V_{SS} , all input/output | llozl | _ | 0.025 | 1.0 | μΑ |
| Internal pullup resistors ² (all port pins) | R _{PU} | 20 | 45 | 65 | kΩ |
| Internal pulldown resistors²(all port pins except PTA5) | R _{PD} | 20 | 45 | 65 | kΩ |
| PTA5 Internal pulldown resistor | _ | 45 | _ | 95 | kΩ |
| Output high voltage — Low Drive (PTxDSn = 0) 5 V, I _{Load} = 2 mA 3 V, I _{Load} = 1 mA 1.8 V, I _{Load} = 0.5 mA | | V _{DD} – 0.8 | _ _ _ | | |
| Output high voltage — High Drive (PTxDSn = 1) 5 V, I _{Load} = 10 mA 5 V, I _{Load} = 5 mA 3 V, I _{Load} = 3 mA 1.8 V, I _{Load} = 2 mA | $\begin{array}{c} \text{ge} - \text{Low Drive (PTxDSn} = 0) \\ \text{mA} \\ \text{ge} - \text{High Drive (PTxDSn} = 1)} \\ \text{A} \\ \text{V}_{\text{OH}} \\ \text{V}_{\text{DD}} - 0.8 \\ \text{A} \\ \text{H for all port pins} \\ \end{array}$ | | _ _ _ _ | _ _ _ _ | V |
| Maximum total IOH for all port pins | I _{OHT} | _ | _ | 40 | mA |
| Output low voltage — Low Drive (PTxDSn = 0) 5 V, I _{Load} = 2 mA 3 V, I _{Load} = 1 mA 1.8 V, I _{Load} = 0.5 mA | | _ _ _ | _ _ _ | 0.8 | |
| Output low voltage — High Drive (PTxDSn = 1) 5 V, I _{Load} = 10 mA 5 V, I _{Load} = 5 mA 3 V, I _{Load} = 3 mA 1.8 V, I _{Load} = 2 mA | V _{OL} | _ _ _ | _ _ _ _ | 0.8 | V |
| Maximum total lo∟ for all port pins | I _{OLT} | _ | _ | 40 | mA |
| DC injection current ^{3, 4, 5, 6} $V_{In} < V_{SS}, V_{In} > V_{DD}$ Single pin limit Total MCU limit, includes sum of all stressed pins | | | | 0.2 0.8 | mA |
| Input capacitance (all non-supply pins) | C _{In} | _ | _ | 7 | pF |

¹ This parameter is characterized and not tested on each device.

 $^{^2}$ Measurement condition for pull resistors: $\rm V_{ln}$ = $\rm V_{SS}$ for pullup and $\rm V_{ln}$ = $\rm V_{DD}$ for pulldown.

³ All functional non-supply pins are internally clamped to V_{SS} and V_{DD} except the \overline{RESET}/V_{PP} which is internally clamped to V_{SS} only.

⁴ Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.

⁵ Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.

⁶ This parameter is characterized and not tested on each device.



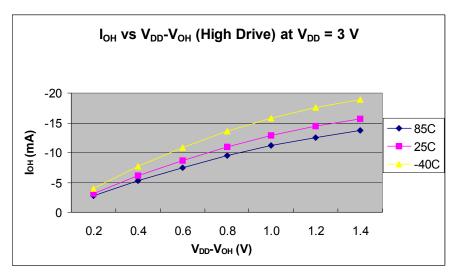


Figure 6. Typical I_{OH} vs. V_{DD} - V_{OH} V_{DD} = 3 V (High Drive)

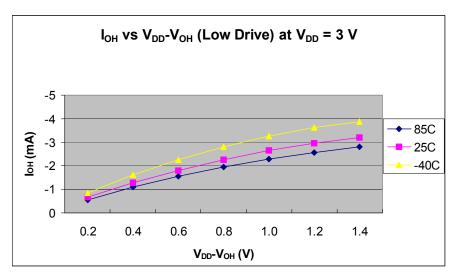


Figure 7. Typical I_{OH} vs. $V_{DD}-V_{OH}$ V_{DD} = 3 V (Low Drive)



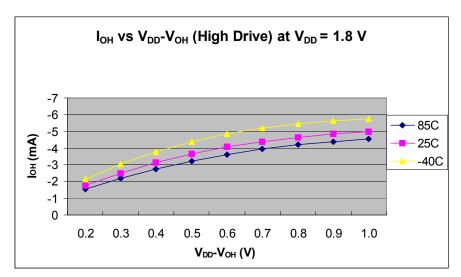


Figure 8. Typical I_{OH} vs. V_{DD} - V_{OH} V_{DD} = 1.8 V (High Drive)

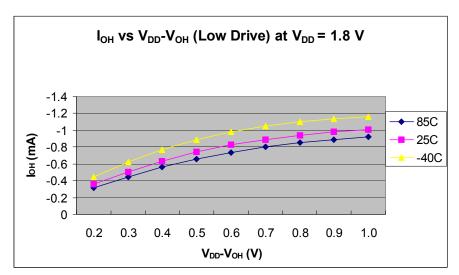


Figure 9. Typical I_{OH} vs. $V_{DD} - V_{OH}$ $V_{DD} = 1.8 \text{ V (Low Drive)}$



3.9.1 Control Timing

Table 10. Control Timing

| Num | С | Parameter | Symbol | Min | Typical | Max | Unit |
|-----|---|--|---------------------------------------|----------------------|----------|------|------|
| 1 | D | Bus frequency (t _{cyc} = 1/f _{Bus}) | f _{Bus} | 0 | _ | 10 | MHz |
| 2 | D | Real time interrupt internal oscillator period | t _{RTI} | 700 | 1000 | 1300 | μS |
| 3 | D | External RESET pulse width ¹ | t _{extrst} | 150 | _ | _ | ns |
| 4 | D | KBI pulse width ² | t _{KBIPW} | 1.5 t _{cyc} | _ | _ | ns |
| 5 | D | KBI pulse width in stop ¹ | t _{KBIPWS} | 100 | _ | _ | ns |
| 6 | D | Port rise and fall time (load = 50 pF) ³ Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1) | t _{Rise} , t _{Fall} | _ | 11 35 | | ns |

¹ This is the shortest pulse guaranteed to pass through the pin input filter circuitry. Shorter pulses may or may not be recognized.

 $^{^3}$ Timing is shown with respect to 20% $\rm V_{DD}$ and 80% $\rm V_{DD}$ levels. Temperature range $-40^{\circ}\rm C$ to 85°C.

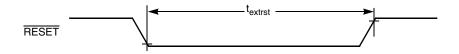


Figure 17. Reset Timing

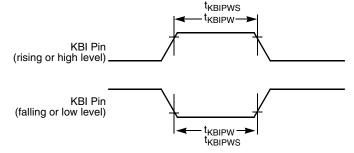


Figure 18. KBI Pulse Width

² This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized in that case.



Table 14. 5 Volt 10-bit ADC Operating Conditions (continued)

| С | Characteristic | Conditions | Symb | Min. | Typical | Max. | Unit |
|---|----------------------|----------------------|-------|------|---------|------|-------|
| D | ADC conversion clock | High Speed (ADLPC=0) | f | 0.4 | _ | 8.0 | MHz |
| | frequency | Low Power (ADLPC=1) | IADCK | 0.4 | _ | 8.0 | IVIMZ |

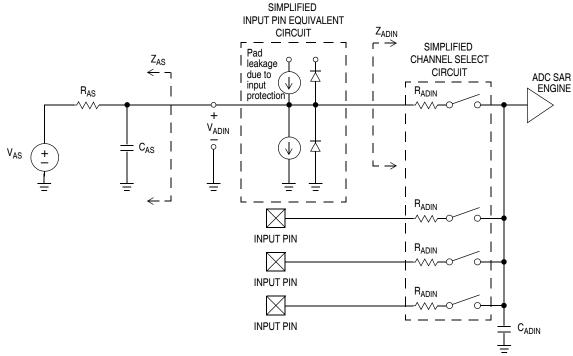


Figure 21. ADC Input Impedance Equivalency Diagram

Table 15. 10-bit ADC Characteristics

| Characteristic | Conditions | С | Symb | Min | Typical ¹ | Max | Unit |
|---|------------|---|-------------------|-----|----------------------|-----|------|
| Supply current ADLPC = 1 ADLSMP = 1 ADCO = 1 | _ | Т | I _{DDAD} | _ | 133 | _ | μΑ |
| Supply current ADLPC = 1 ADLSMP = 0 ADCO = 1 | _ | Т | I _{DDAD} | _ | 218 | | μΑ |
| Supply current ADLPC = 0 ADLSMP = 1 ADCO = 1 | _ | Т | I _{DDAD} | _ | 327 | | μΑ |
| Supply current ADLPC = 0 ADLSMP = 0 ADCO = 1 | _ | С | I _{DDAD} | _ | 0.582 | 1 | mA |

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Table 15. 10-bit ADC Characteristics (continued)

| Characteristic | Conditions | С | Symb | Min | Typical ¹ | Max | Unit | | | |
|--------------------------------|--|----------|-------------------|-----|----------------------|------|--------------------|--|--|--|
| Supply current | Stop, reset, module off | Т | I _{DDAD} | _ | 0.011 | 1 | μА | | | |
| ADC asynchronous clock | High speed (ADLPC = 0) | | 4 | _ | 3.3 | _ | NALI | | | |
| source | Low power (ADLPC = 1) | T FADACK | | _ | 2 | _ | MHz | | | |
| Conversion time (including | Short sample (ADLSMP=0) | Р | | _ | 20 | _ | ADCK | | | |
| sample time) | Long sample (ADLSMP=1) | | t _{ADC} | _ | 40 | _ | cycles | | | |
| Sample time | Short sample (ADLSMP=0) | Р | + | _ | 3.5 | _ | ADCK | | | |
| Sample time | Long sample (ADLSMP=1) |] [| t _{ADS} | _ | 23.5 | _ | cycles | | | |
| Total unadjusted error | 10 bit mode | С | F | _ | ±1 | ±2.5 | - LSB ² | | | |
| Total unaujusteu error | 8 bit mode | | E _{TUE} | _ | ±0.5 | ±1.0 | | | | |
| Differential non-linearity | 10 bit mode | Р | DNL | _ | ±0.5 | ±1.0 | LSB ² | | | |
| | 8 bit mode | Т | DIVL | _ | ±0.3 | ±0.5 | | | | |
| | Monotonicity and No-Missing-Codes guaranteed | | | | | | | | | |
| Integral non-linearity | 10 bit mode | С | INL | _ | ±0.5 | ±1.0 | LSB ² | | | |
| megrai non-imeamy | 8 bit mode | | IINL | _ | ±0.3 | ±0.5 | LOD | | | |
| Zero-scale error | 10 bit mode | Р | E _{ZS} | _ | ±0.5 | ±1.5 | LSB ² | | | |
| Zeio-scale eiioi | 8 bit mode | Т | ⊏ZS | _ | ±0.5 | ±0.5 | LOD | | | |
| Full-Scale error | 10 bit mode | Р | _ | _ | ±0.5 | ±1.5 | LSB ² | | | |
| VADIN = VDDA | 8 bit mode | Т | E _{FS} | _ | ±0.5 | ±0.5 | LOD | | | |
| Quantization error | 10 bit mode | D | E. | _ | _ | ±0.5 | LSB ² | | | |
| | 8 bit mode | ן ד | D E _Q | _ | _ | ±0.5 | LOD | | | |
| Input leakage error | 10 bit mode | D | _ | _ | ±0.2 | ±2.5 | LSB ² | | | |
| pad leakage ³ * RAS | 8 bit mode | ן כ | E _{IL} | _ | ±0.1 | ±1 | | | | |

Typical values assume Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

3.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the flash memory. For detailed information about program/erase operations, see the reference manual.

Table 16. Flash Characteristics

| Characteristic | Symbol | Min | Typical ¹ | Max | Unit |
|----------------------------------|----------|-----|----------------------|-----|------|
| Supply voltage for program/erase | V_{DD} | 2.7 | _ | 5.5 | V |

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² 1 LSB = $(V_{REFH} - V_{REFL})/2^N$

³ Based on input pad leakage current. Refer to pad electrical.



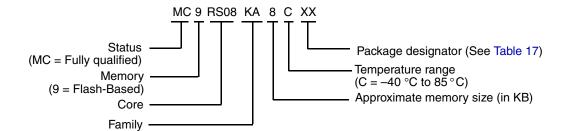
Ordering Information

4 Ordering Information

This section contains ordering numbers for MC9RS08KA8 series devices. See below for an example of the device numbering system.

| Device Number | Men | nory | Package | | | |
|---------------|---|--------------------|-----------|------------|--------------|--|
| Device Number | Flash RAM | | Туре | Designator | Document No. | |
| | | 8K bytes 254 bytes | 16 PDIP | PG | 98ASB42431B | |
| | MC9RS08KA8 MC9RS08KA4 8K bytes 4K bytes | | 16 W-SOIC | WG | 98ASB42567B | |
| | | 126 bytes | 16 TSSOP | TG | 98ASH70247A | |
| | | | 20 PDIP | PJ | 98ASB42899B | |
| 1 | | | 20 W-SOIC | WJ | 98ASB42343B | |

Table 17. Device Numbering System



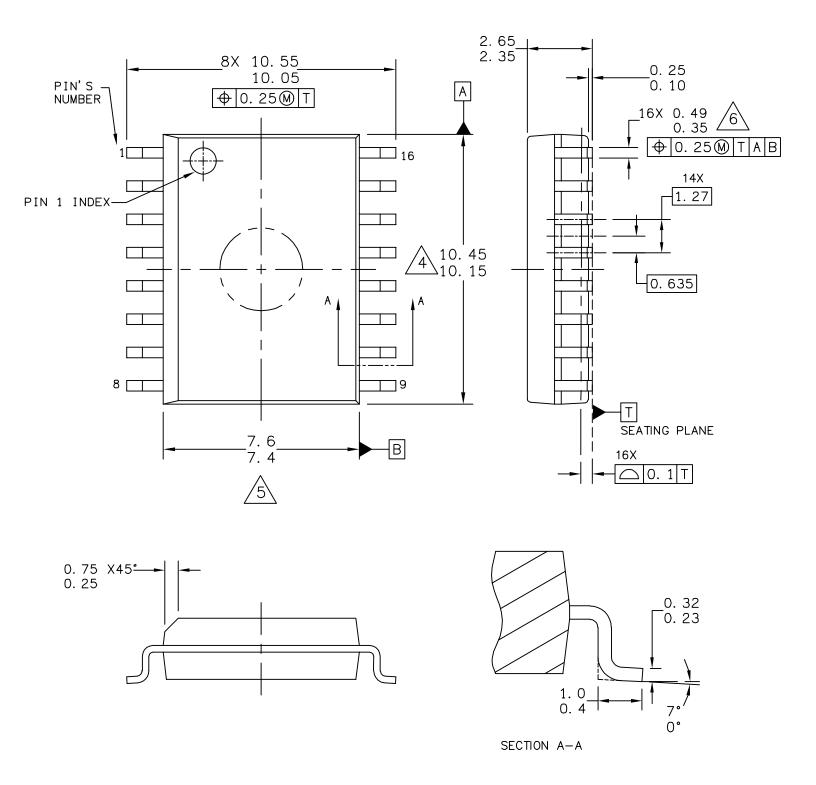
5 Mechanical Drawings

This following pages contain mechanical specifications for MC9RS08KA8 series package options.

- 16-pin PDIP (plastic dual in-line pin)
- 16-pin W-SOIC (wide body small outline integrated circuit)
- 16-pin TSSOP (thin shrink sSmall outline package)
- 20-pin PDIP (plastic dual in-line pin)
- 20-pin W-SOIC (wide body small outline integrated circuit)

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|--|-----------|-----------------------------|------------------|-------------|
| TITLE: | 07 017011 | DOCUMENT NO |): 98ASB42567B | REV: F |
| 16LD SOIC W/B, 1.27 PITCH CASE-OUTLINE | | CASE NUMBER: 751G-04 02 JUN | | |
| CASL-OOTE1 | INL | STANDARD: JE | DEC MS-013AA | |

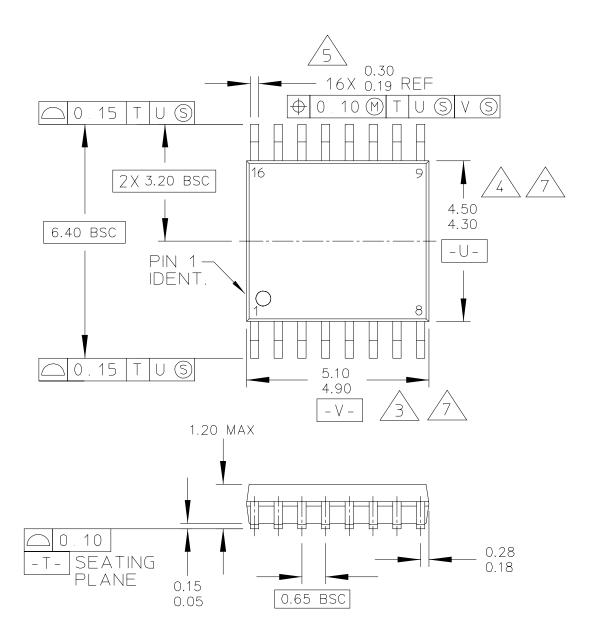


NOTES:

- 1. DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 3. DATUMS A AND B TO BE DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- THIS DIMENSION DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSION OR GATE BURRS SHALL NOT EXCEED 0.15 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- THIS DIMENSION DOES NOT INCLUDE INTER—LEAD FLASH OR PROTRUSIONS. INTER—LEAD FLASH AND PROTRUSIONS SHALL NOT EXCEED 0.25 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.62 mm.

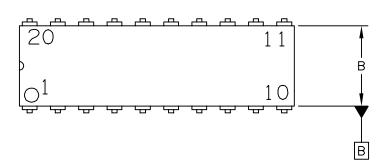
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|--|--------------|--------------|------------------|-------------|
| TITLE: | - | DOCUMENT NO |): 98ASB42567B | REV: F |
| 16LD SOIC W/B, 1.2° Case outline | • | CASE NUMBER | R: 751G-04 | 02 JUN 2005 |
| CASE OUTETNE | _ | STANDARD: JE | IDEC MS-013AA | |

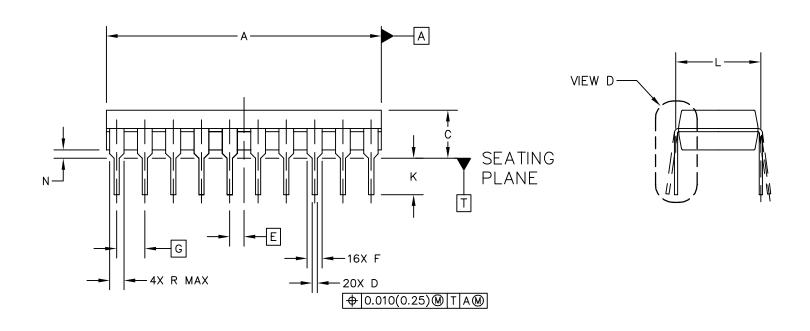




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|--|-----------|--------------|------------------|----------|
| TITLE: | | DOCUMENT NO | REV: B | |
| 16 LD TSSOP, PITCH 0.6 | 5MM | CASE NUMBER | 19 MAY 2005 | |
| | | STANDARD: JE | DEC | |







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|--|-----------|------------------|----------------|-------------|
| TITLE: | | DOCUMENT NO | l: 98ASB42899B | REV: B |
| 20LD .300 PDIF |) | CASE NUMBER | 2: 738C−01 | 24 MAY 2005 |
| 2010 .300 1 011 | | STANDARD: NO | IN-JEDEC | |



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

20LD .300 PDIP

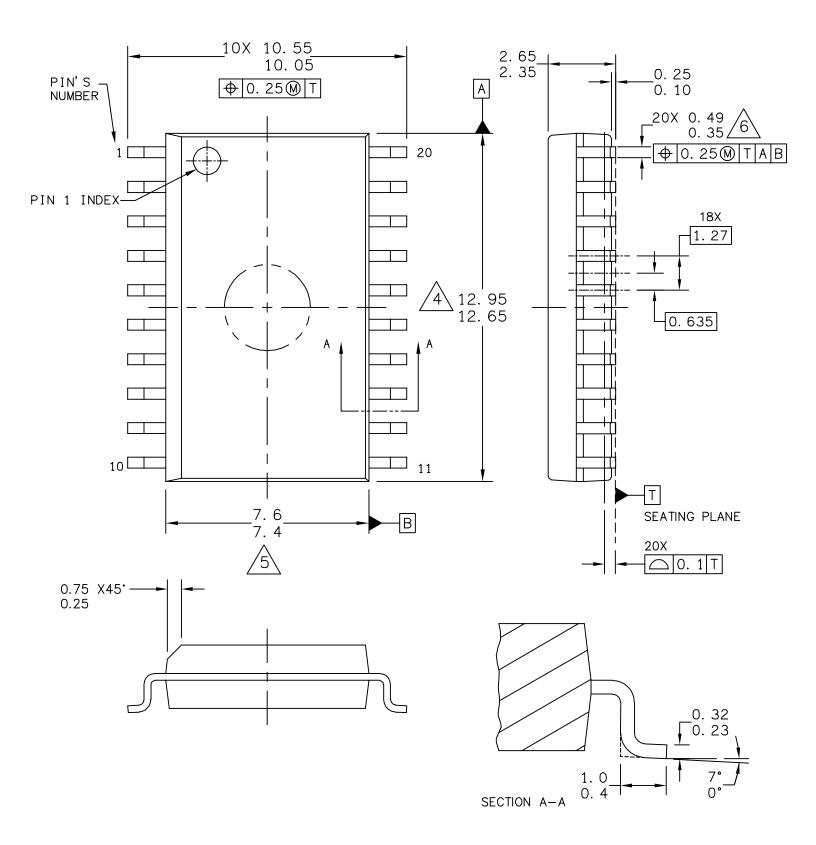
| DIM | MILLIME MIN | ETERS MAX | DIM | IN MIN | CHES MAX | DIM | MILLIME MIN | ETERS MAX | DIM | М | INCHE In | ES MAX |
|--|----------------|--------------|---------|-----------|-------------|---------|----------------|--------------|------|-------|-------------|-----------|
| Α | 24.39 | 24.99 | | 0.960 | 0.984 | | | | | | | |
| В | 6.96 | 7.49 | | 0.274 | 0.295 | | | | | | | |
| С | 3.56 | 5.08 | | 0.140 | 0.200 | | | | | | | |
| D | 0.38 | 0.56 | | 0.015 | 0.022 | | | | | | | |
| E | 1.27 E | 3SC | | 0.050 | D BSC | | | | | | | |
| F | 1.14 | 1.52 | | 0.045 | 0.060 | | | | | | | |
| G | 2.54 E | 3SC | | 0.100 | D BSC | | | | | | | |
| J | 0.20 | 0.38 | | 0.008 | 0.015 | | | | | | | |
| K | 2.79 | 3.76 | | 0.110 | 0.148 | | | | | | | |
| L | 7.62 BS | SC | | 0.300 | BSC | | | | | | | |
| М | 0. | 15° | | 0. | 15° | | | | | | | |
| N | 0.50 | 1.01 | | 0.020 | 0.040 | | | | | | | |
| R | ••••• | 1.29 | | •••• | 0.051 | | | | | | | |
| | | | | | | | | | | | | |
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| TITLE: DOCUMENT NO: 98ASB42899B REV: B | | | | | 3 | | | | | | | |

CASE NUMBER: 738C-01

STANDARD: NON-JEDEC

24 MAY 2005





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|--|-------------|--------------|------------------|-------------|
| TITLE: | 07 017011 | | : 98ASB42343B | REV: J |
| 20LD SOIC W/B, 1. CASE-OUTLI | CASE NUMBER | : 751D-07 | 23 MAR 2005 | |
| | INL | STANDARD: JE | DEC MS-013AC | |







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